



UT4414

Power MOSFET

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

DESCRIPTION

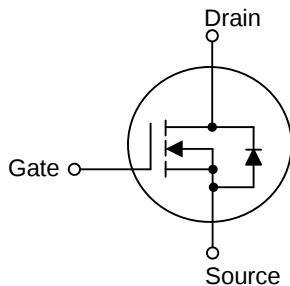
The UTC **UT4414** is an N-channel enhancement mode FET with excellent trench technology to provide customers perfect $R_{DS(ON)}$ and low gate charge. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.

This device can be applied in a load switch or in PWM applications.

FEATURES

- * $V_{DSS} = 30V$
- * $I_D = 8.5A$ @ $V_{GS} = 10V$
- * $R_{DS(ON)} \leq 26m\Omega$ @ $V_{GS} = 10V, I_D = 8.5A$
- * $R_{DS(ON)} \leq 40m\Omega$ @ $V_{GS} = 4.5V, I_D = 5.0A$

SYMBOL

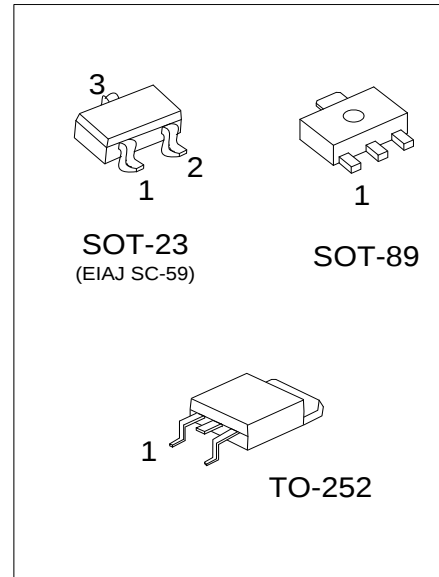


ORDERING INFORMATION

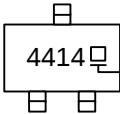
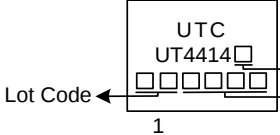
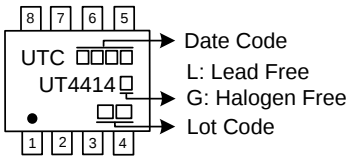
Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UT4414L-AE3-R	UT4414G-AE3-R	SOT-23	G	S	D	-	-	-	-	-	Tape Reel
UT4414L-TN3-R	UT4414G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
UT4414L-S08-R	UT4414G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

UT4414G-AE3-R (1) Packing Type (2) Package Type (3) Green Package		(1) R: Tape Reel (2) AE3: SOT-23, TN3: TO-252, S08: SOP-8 (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING

PACKAGE	MARKING
SOT-23	
TO-252	
SOP-8	

■ ABSOLUTE MAXIMUM RATING ($T_A = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain to Source Voltage		V_{DS}	30	V
Gate to Source Voltage		V_{GS}	± 20	V
Continuous Drain Current		I_D	8.5	A
Pulsed Drain Current		I_{DM}	50	A
Avalanche Energy (Note 3)	Single Pulsed	E_{AS}	11	mJ
Total Power Dissipation	SOT-23	P_D	1.5	W
	TO-252		2.5	W
	SOP-8		2.1	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
 3. $L = 0.1\text{mH}$, $I_{AS} = 13\text{A}$, $V_{DD} = 25\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-23	θ_{JA}	83.3	$^\circ\text{C/W}$
	TO-252		50	$^\circ\text{C/W}$
	SOP-8		59	$^\circ\text{C/W}$

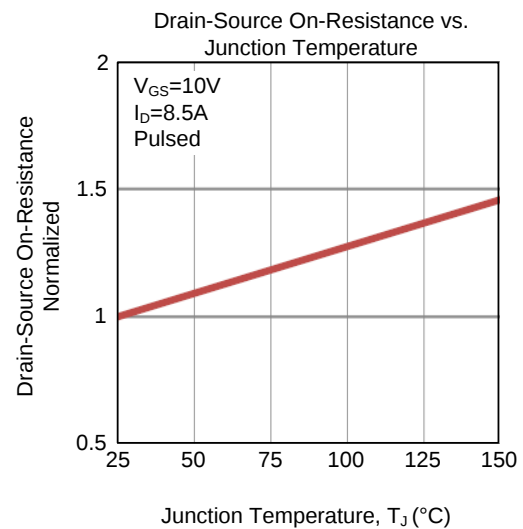
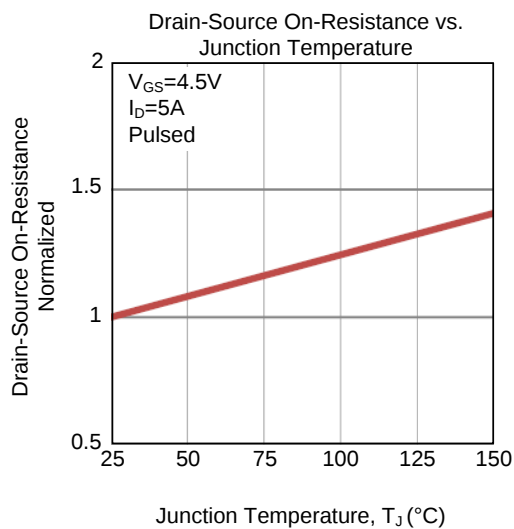
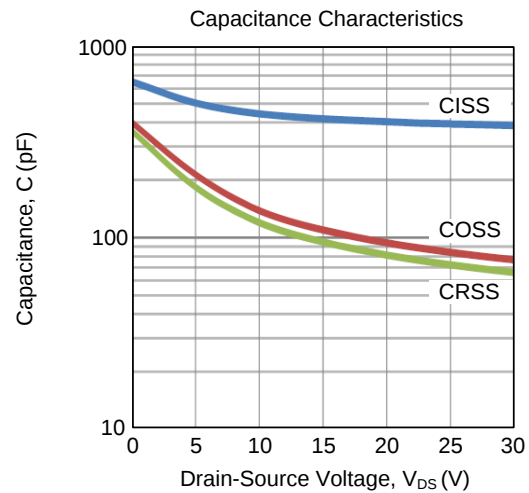
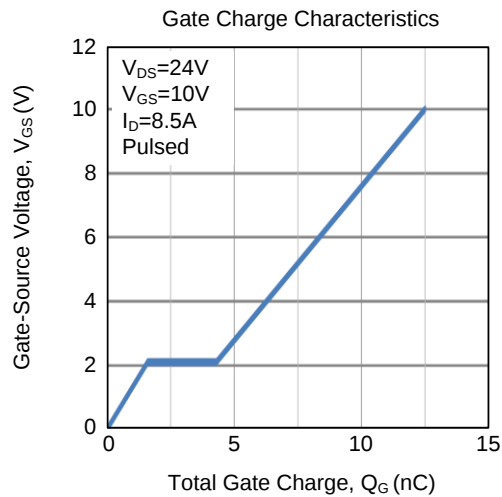
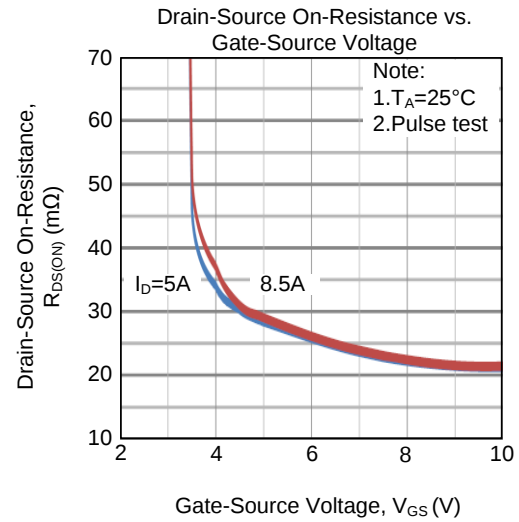
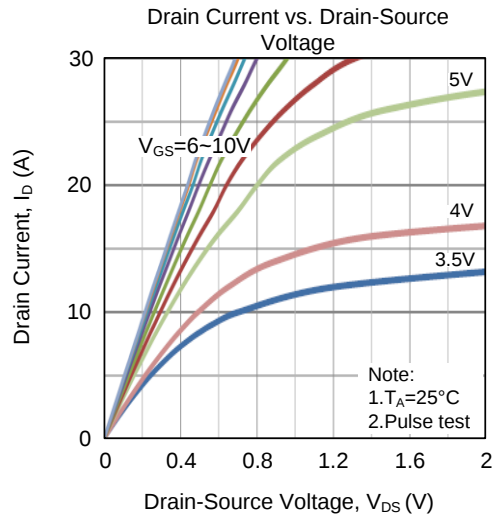
- Notes: 1. The value of θ_{JA} is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.
 2. The θ_{JA} is the sum of the thermal impedance from junction to lead θ_{JL} and lead to ambient.

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

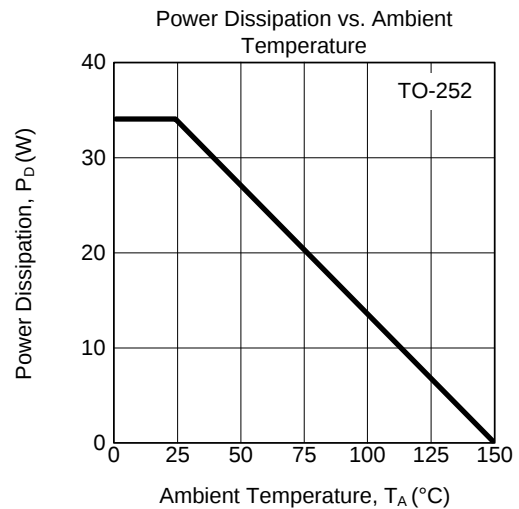
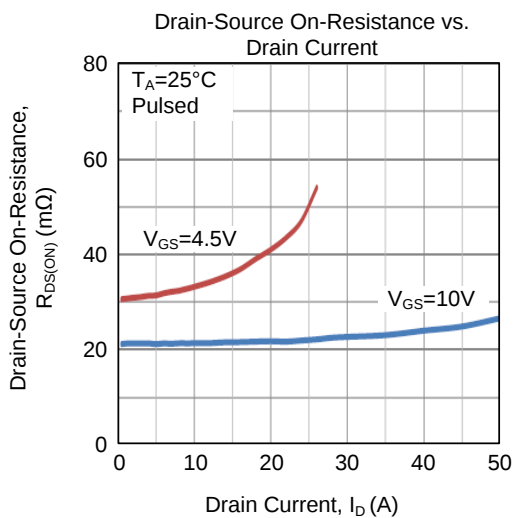
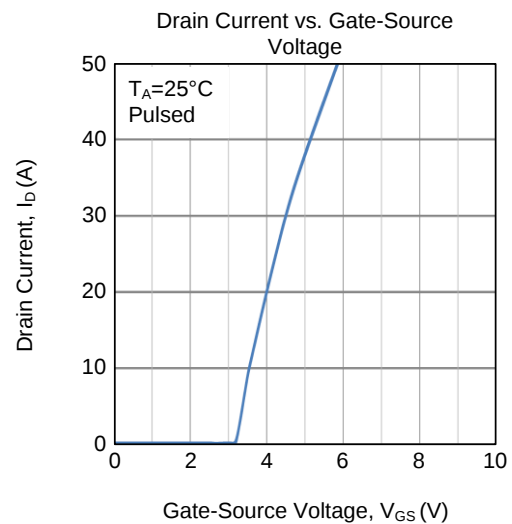
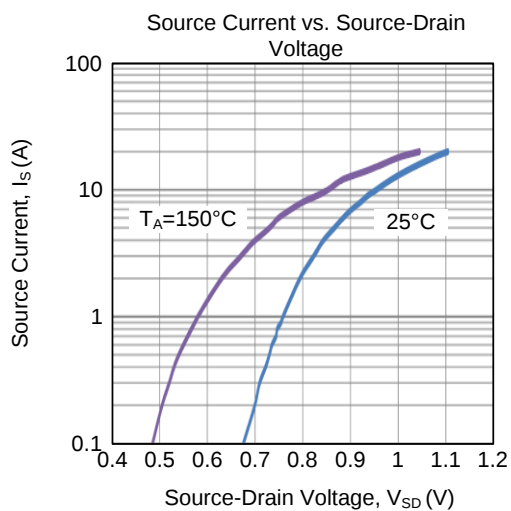
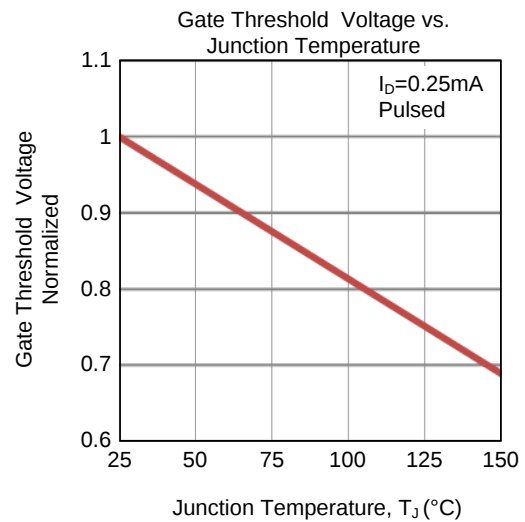
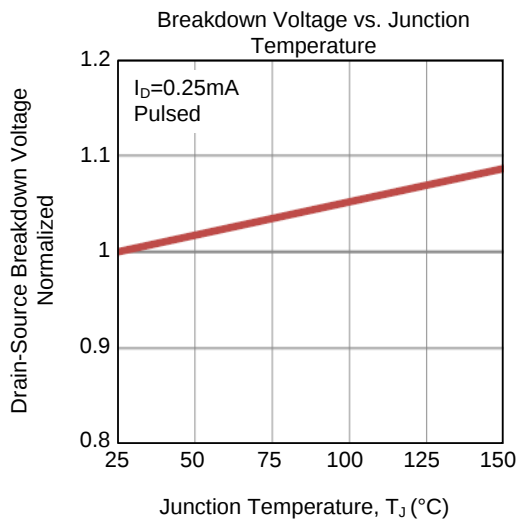
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	30			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V		0.004	1	μA
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V , V _{GS} =±20V			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D =250μA	1.0	1.9	3.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =8.5A		20	26	mΩ
		V _{GS} =4.5V, I _D =5.0A		31	40	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V, f=1MHz		420		pF
Output Capacitance	C _{OSS}			110		pF
Reverse Transfer Capacitance	C _{RSS}			95		pF
Gate Resistance	R _G	V _{DS} =0V, V _{GS} =0V, f=1MHz			3.6	Ω
SWITCHING PARAMETERS						
Total Gate Charge	Q _G	V _{DS} =24V, V _{GS} =10V, I _D =8.5A		12.4		nC
Gate-Source Charge	Q _{GS}			1.6		nC
Gate-Drain Charge	Q _{GD}			2.7		nC
Turn-ON Delay Time	t _{D(ON)}	V _{DS} =15V, V _{GS} =10V, I _D =8.5A R _G =3Ω		3.6		ns
Turn-ON Rise Time	t _R			16		ns
Turn-OFF Delay Time	t _{D(OFF)}			15		ns
Turn-OFF Fall Time	t _F			19		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I _S				4.3	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V		0.76	1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F =8.5A, dI/dt=100A/μs		204		ns
Body Diode Reverse Recovery Charge	Q _{rr}	I _F =8.5A, dI/dt=100A/μs		390		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

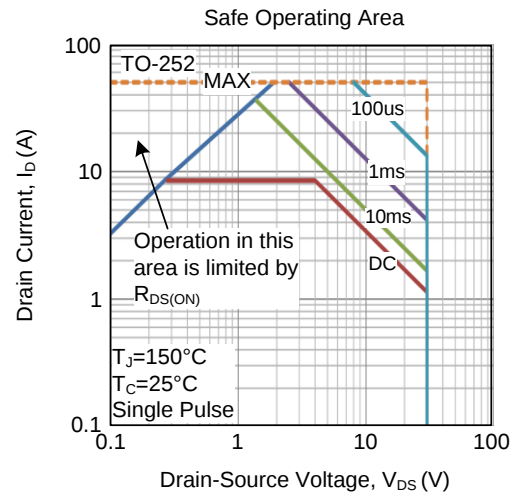
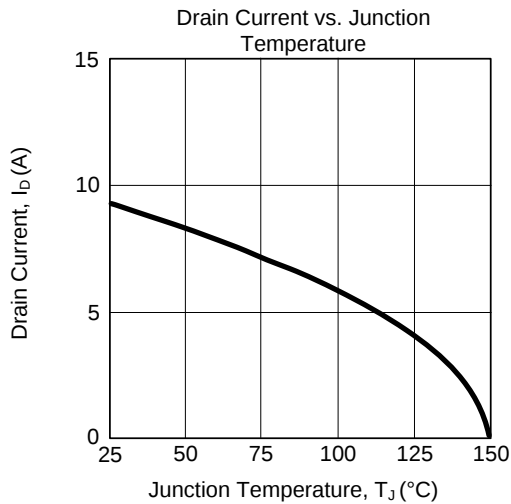
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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